

In the Specification:

Please amend the specification as follows:

Page 4, line 3:

According to an aspect of the invention, an oxide layer is already formed on the semiconductor substrate. And the oxide layer is formed to a thickness of about 50 angstrom to about 200 angstrom. The first conductive layer and the second conductive layer is a doped polysilicon layer.

Page 4, line 7:

According to a preferred embodiment of the present invention, the dielectric layer is multi-layer including an oxide layer and a nitride layer and the dielectric layer is formed to a thickness of about 100 angstrom to about 200 angstrom.

Page 5, line 3:

According to a preferred aspect of the present invention, the silicide layer is a silicide selected from the silicide group consisting of cobalt silicide (CoSix), tungsten silicide (~~Wsix~~ WSix) and aluminum silicide (AlSix).